

# Corrigendum to “Optimization of charge and multiplication layers of 20-Gbps InGaAs/InAlAs avalanche photodiode”

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In the article entitled “Optimization of charge and multiplication layers of 20-Gbps InGaAs/InAlAs avalanche photodiode,” the authors would like to correct the acknowledgments of their article. It should be written as follows:

## **ACKNOWLEDGMENTS**

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The authors would like to apologize for the inconvenience caused.

## **CONFLICTS OF INTEREST**

The authors declare that there are no conflicts of interest.